

**Family list****12** family members for:**JP2001168458**

Derived from 9 applications.

**1 Semiconductor laser device and method of manufacture thereof**Publication info: **EP1263100 A2** - 2002-12-04**EP1263100 A3** - 2005-02-09**2 SEMICONDUCTOR LASER**Publication info: **JP2001168458 A** - 2001-06-22**3 SEMICONDUCTOR LASER AND MANUFACTURING METHOD**Publication info: **JP2003051641 A** - 2003-02-21**4 SEMICONDUCTOR LASER DEVICE**Publication info: **JP2003069148 A** - 2003-03-07**5 High-power semiconductor laser device in which near-edge portions of active layer are removed**Publication info: **TW507401 B** - 2002-10-21**6 Semiconductor laser device and manufacturing method for the same**Publication info: **TW533633 B** - 2003-05-21**7 High-power semiconductor laser device in which near-edge portions of active layer are removed**Publication info: **US6580738 B2** - 2003-06-17**US2002015428 A1** - 2002-02-07**8 Semiconductor laser device**Publication info: **US6856636 B2** - 2005-02-15**US2003039289 A1** - 2003-02-27**9 High-power semiconductor laser device in which near-edge portions of active layer are removed**Publication info: **US2001017871 A1** - 2001-08-30

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	("6798808").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 10:58
L4	0	"2001017871" "2001017875"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 10:59
L3	6	(("2001017871") or ("2001017875")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/24 10:59
L8	96	7 and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:00
L7	297	fukunaga near2 toshiaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:00
L10	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film)) and (fukunaga near2 toshiaki.in. )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:02
L11	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film)) and (fukunaga near2 toshiaki.in. )	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:03
L16	61	(Yamamoto near2 Kei) or (Ohbayashi near2 Ken).in. and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:06
L15	66	(Yamamoto near2 Kei) or (Ohbayashi near2 Ken).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:06
L18	5	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film)) and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:09
L21	139	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier) and (guide near2 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:10

L20	141	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:10
L22	17	21 and (InGaP or InGaAsP or GaAsP) and ("Al" near5 "Ga" near5 "AS")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:11
L24	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film)) and 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:19
L1	37	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:19
L26	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:20
L25	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film)) and 23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:20
L19	7	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier) and (guide near3 (layer or medium or region or film)) and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:21
L14	37	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:21
L27	42	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:23
L33	2	("20030122134"   "5762705").PN. OR ("6670643").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/10/24 11:26
L31	2	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and (clad\$4 with AL) and (substrate near GaAs) and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:26
L30	3	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and (clad\$4 with AL) and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:26

L29	13	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and (clad\$4 with AL) and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:32
L36	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film) near5 Al near4 Ga near4 As)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:33
L35	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film) near5 "Al" near4 "Ga" near4 "As")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:33
L34	18	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near3 (layer or medium or region or film) near5 AlGaAs)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:38
L37	42	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 11:39
L38	22	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and clad\$4 and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:32
L41	4	ekawa.in. and "372"/\$.ccls.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:33
L39	0	((quantum near2 well) or QW) with (strain\$3 or stain\$3)) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device)) and active and (clad\$4 near3(AlGa)) and substrate and (barrier near3 (InGaP or InGaAsP or GaAsP)) and (guide near2 (layer or medium or region or film))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:33
L42	7	ekawa.in. and (cladding or clad\$4) and guide	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:34
L40	65	ekawa.in.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:34
L23	7	"6580738"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:36
L43	7	"6580738" and (cladding or clad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:54

L44	2	"6580738" and (cladding or clad) and active and substrate and barrier and (well near3 quantum) and strain and (guide or waveguide) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED or (emit\$4 near2 device))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 13:58
L45	1	"6580738" and (cladding or clad) and active and substrate and barrier and (well near3 quantum) and strain and (guide or waveguide) and ((light near3 emit\$4 near2 device) or (light-emit\$4 near2 device) or LED)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 14:01
L47	1	"6580738" and (cladding or clad) and active and substrate and barrier and (well near3 quantum) and strain and (guide) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 14:02
L46	2	"6580738" and (cladding or clad) and active and substrate and barrier and (well near3 quantum) and strain and (guide or waveguide) and ((light ADJ3 emit\$4 ADJ3 device) or (light-emit\$4 ADJ3 device) or LED)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/10/24 14:02